

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L4	977	(polysilicon or polySi or (polycrystalline adj (Si or silicon))) with (CMP or polish\$6) with (detect\$6 or endpoint or (end adj point) or polishstop or stop\$6 or etchstop)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/29 06:21
L5	959	4 and (@ad<="20040129" or @rlad<="20040129")	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/29 06:21
L7	480	5 and (memory or antifuss\$6 or (anti adj fuss\$6))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/29 06:21


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Enter keywords or phrases, select fields, and select operators

<input type="text"/>	in	All Fields	⬇
AND <input type="text"/>	in	All Fields	⬇
AND <input type="text"/>	in	All Fields	⬇

**OPTION 2**

Enter keywords, phrases, or a Boolean expression

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<or> cmj, polish* <and> <or>
(polysilicon or silicon or polysi ) <and>
<or> endpoint, detect*, hdp, hdpowd, hdp-
owd, oxide, sio2, sin)

```

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Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	53564	((polysilicon or polySi or silicon or conductive or metal) near10 (layer or line or film)) and (CMP or polish\$6) and (detects6 or endpoint or (end adj point) or polishstop or stops6 or etchstop or SiN or ((Si or silicon) adj nitride) or Si3N4 or (Si?sub\$3 adj N?sub\$3))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/29 08:01
L2	4527	1 and (HDP or HDPCvD or (high adj density adj plasma))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/29 08:02
L3	4428	2 and (@ad<="20040129" or @rlad<="20040129")	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/29 08:04
L4	4556	(HDP or HDPCvD or (high adj density adj plasma)) and (polish\$6 or CMP) and (polysilicon or polySi or ((poly or polycrylline) near5 (Si or silicon)) or conductor or bitline or (bit adj line) or wiring or interconnect\$6)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/29 08:03
L5	3975	L4 and (stops6 or etchstop or polishstop or mask or hardmask or endpoint or detects6)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/29 08:03
L6	3896	L5 and (IC or (integrated adj circuit) or semiconductor)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/29 08:03
L7	3810	L6 and (@ad<="20040129" or @rlad<="20040129")	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/29 08:03
L8	6284	(HDP or HDPCvD or (high adj density adj plasma)) same (oxide or SiO2 or SiO?sub\$2 or dioxide or glass or silicate)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/29 08:03

L9	293S	L7 and LS	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005.04.29 08:03
L10	1749	3 not 9	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/29 08:04